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Joint ICTP-IAEA Workshop on Physics of Radiation Effect and its Simulation for Non-Metallic Condensed Matter | (smr 2359)

Thursday 16 August 2012

**Electrically active defects in semiconductors induced by radiation - Adriatico Guest House
Kastler Lecture Hall (11:00-12:30)**

In this talk, an overview of the current research on electrically active defects in semiconductors introduced by ion implantation, electron, neutron and Gamma-radiation will be presented. The fundamental differences between damage introduced by those sources, from point-like to cluster-related defects, will be shown. The application of capacitance transient techniques such as Deep Level Transient Spectroscopy (DLTS) and high resolution Laplace DLTS for studying the electrically active defects will be explained. The invention of DLTS, and later an improvement with Laplace DLTS which gives an order of magnitude better energy resolution has meant an enormous breakthrough in the study of electrically active radiation defects in semiconductors.

time	title	presenter
11:00	Electrically active defects in semiconductors induced by radiation	IVANA CAPAN